YJ Planar Schottky Barrier Diode Die Specification

40V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process

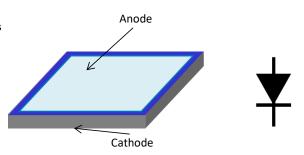
Part No.: PSB025L040AS-180A

Main Products Characterstics

• Average forward current: IF(AV) = 0.5 A

• Maximum operating junction temperature: Tj = 125 °C

• Top metal: AL



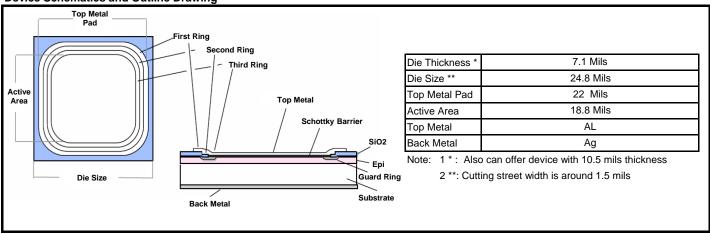
Maximum Ratings

Parameter	Symbol	Rating		
Repetitive peak reverse voltage	V_{RRM}	40 V		
Average forward current	I _{F(AV)}	0.5 A		
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	10 A		
Storage temperature range	T_{stg}	-50 to +125 °C		
Maximum operating junction temperature	Tj	125 °C		

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1 \text{mA}$	V_{BR}	45 V	52V
Maximum forward voltage drop			
$I_F = 0.5 A$	V_{F}	0.535V	0.45V
Pulse Test: tp = 300 μ s, $\delta \leqslant 2\%$			
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: tp = 300 μ s, $\delta \leqslant 2\%$	I _R	20uA	3uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangile Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

扬州扬杰电子科技股份有限公司

Yangzhou Yangjie Electronics Technology Co.,Ltd.

电话: 0514-80982389

传真: 0514-80980189